

# MOSFET – N-Channel, Logic Level, **POWERTRENCH®**

**60 V, 1.6 A, 98 mΩ**

## FDN5632N-F085

### Features

- $R_{DS(on)} = 98\text{ m}\Omega$  at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 1.6\text{ A}$
- $R_{DS(on)} = 82\text{ m}\Omega$  at  $V_{GS} = 10\text{ V}$ ,  $I_D = 1.7\text{ A}$
- Typ  $Q_{g(TOT)} = 9.2\text{ nC}$  at  $V_{GS} = 10\text{ V}$
- Low Miller Charge
- UIS Capability
- AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free, Halide Free and is RoHS Compliant

### Applications

- DC/DC Converter
- Motor Drives

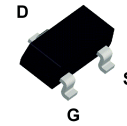
### MOSFET MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain to Source Voltage	60	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current Continuous ( $V_{GS} = 10\text{ V}$ )	1.7	A
	Pulsed	10	
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	74	mJ
$P_D$	Power Dissipation	1.1	W
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to +150	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	75	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252, 1 in <sup>2</sup> Copper Pad Area	111	$^\circ\text{C/W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

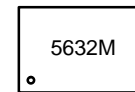
1.  $E_{AS}$  of 74 mJ is 100% test at  $L = 80\text{ mH}$ ,  $I_{AS} = 1.4\text{ A}$ , starting  $T_J = 25^\circ\text{C}$

$V_{DSS}$	$r_{DS(on)}$ MAX	$I_D$ MAX
60 V	82 mΩ @ 10 V	1.6 A
	98 mΩ @ 4.5 V	



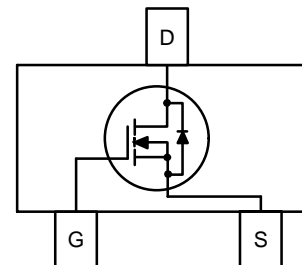
SOT-23/SUPERSOT™ -23, 3 LEAD, 1.4x2.9  
CASE 527AG

### MARKING DIAGRAM



5632 = Specific Device Code  
M = Date Code

### PIN ASSIGNMENT



### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# FDN5632N-F085

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

B <sub>V</sub> DSS	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	60	–	–	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V	–	–	1	μA
		V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>A</sub> = 125°C	–	–	250	
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20 V	–	–	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1	2.0	3	V
r <sub>DS(on)</sub>	Drain to Source On Resistance	I <sub>D</sub> = 1.7 A, V <sub>GS</sub> = 10 V	–	57	82	mΩ
		I <sub>D</sub> = 1.6 A, V <sub>GS</sub> = 6 V	–	62	88	
		I <sub>D</sub> = 1.6 A, V <sub>GS</sub> = 4.5 V	–	70	98	
		I <sub>D</sub> = 1.7 A, V <sub>GS</sub> = 10 V, T <sub>A</sub> = 150°C	–	107	135	

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	475	–	pF
C <sub>oss</sub>	Output Capacitance		–	60	–	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	30	–	pF
R <sub>G</sub>	Gate Resistance	f = 1MHz	–	1.4	–	Ω
Q <sub>g(TOT)</sub>	Total Gate Charge at 10 V	V <sub>GS</sub> = 0 to 10 V, V <sub>DD</sub> = 20 V, I <sub>D</sub> = 1.7 A	–	9.2	12	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>DD</sub> = 20 V, I <sub>D</sub> = 1.7 A	–	1.5	–	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		–	1.4	–	nC

### SWITCHING CHARACTERISTICS

t <sub>on</sub>	Turn-On Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 1.0 A V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω	–	–	30	ns
t <sub>d(on)</sub>	Turn-On Delay Time		–	15	–	ns
t <sub>r</sub>	Rise Time		–	1.7	–	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		–	5.2	–	ns
t <sub>f</sub>	Fall Time		–	1.3	–	ns
t <sub>off</sub>	Turn-Off Time		–	–	12.9	ns

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Source to Drain Diode Voltage	I <sub>SD</sub> = 1.7 A	–	0.8	1.25	V
		I <sub>SD</sub> = 0.85 A	–	0.8	1.0	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> = 1.7 A, dI <sub>SD</sub> /dt = 100 A/μs	–	16.0	21	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	7.9	10.3	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

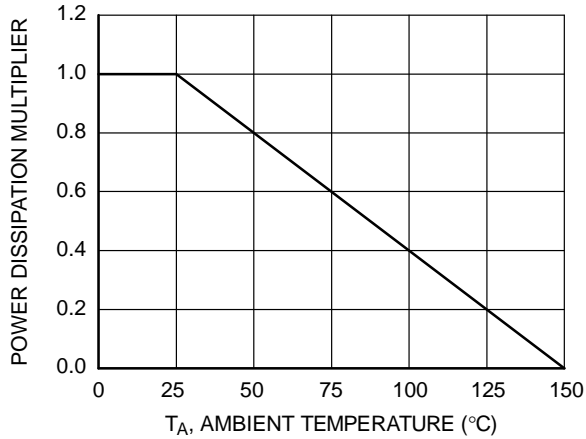


Figure 1. Normalized Power Dissipation vs. Case Temperature

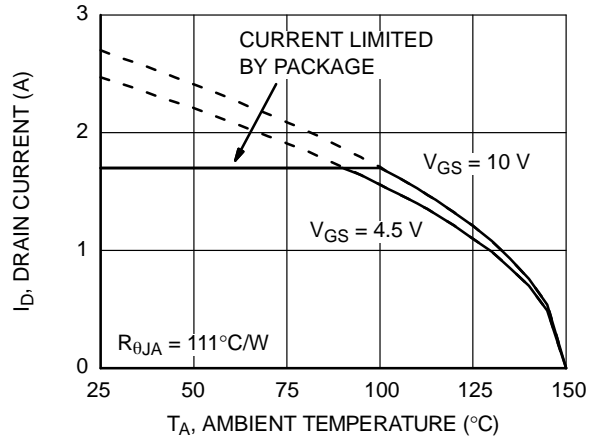


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

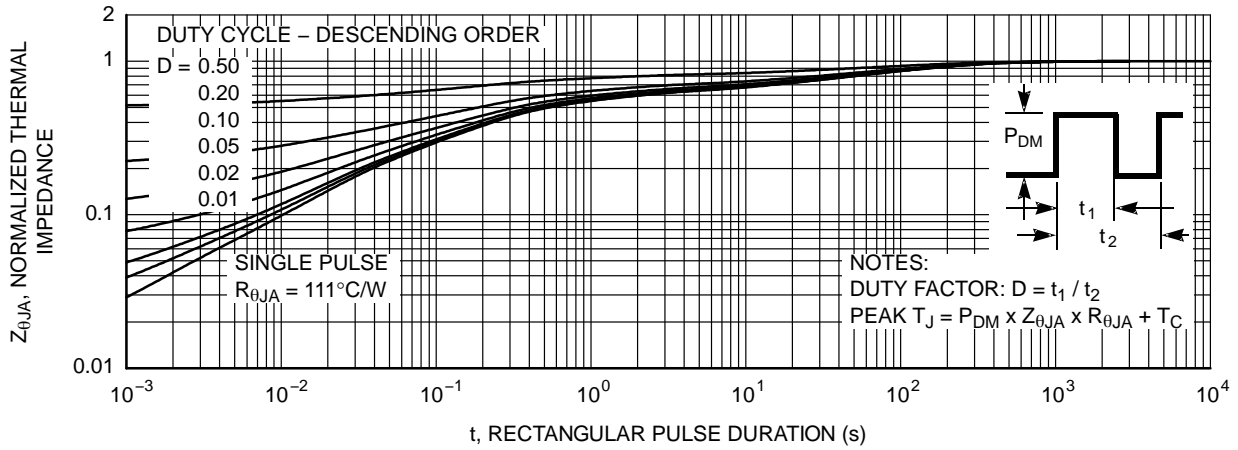


Figure 3. Normalized Maximum Transient Thermal Impedance

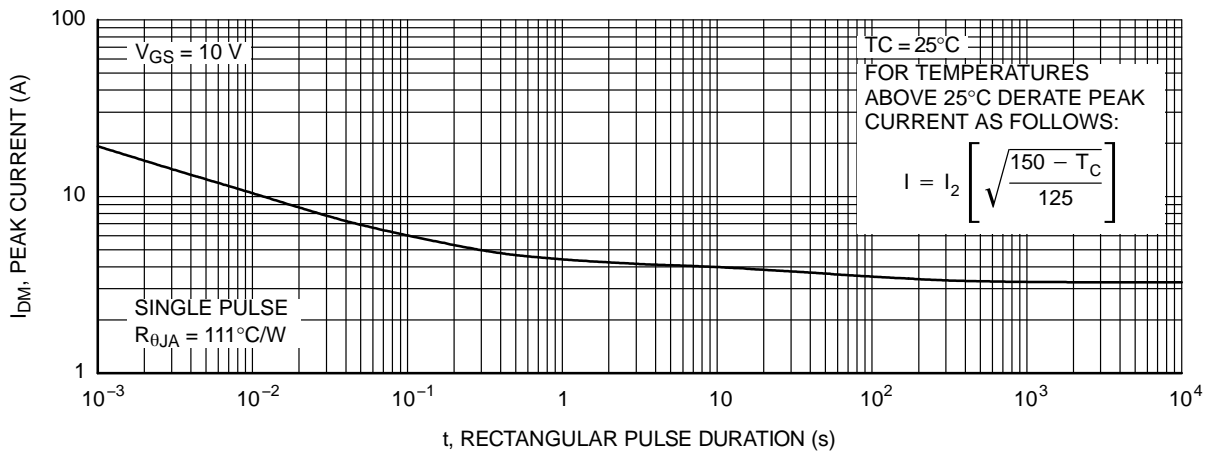


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS

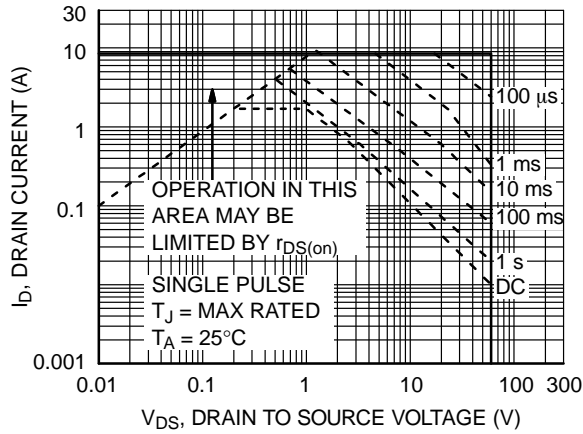


Figure 5. Forward Bias Safe Operating Area

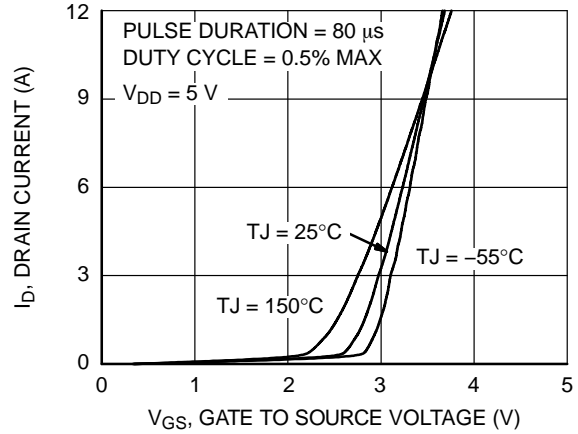


Figure 6. Transfer Characteristics

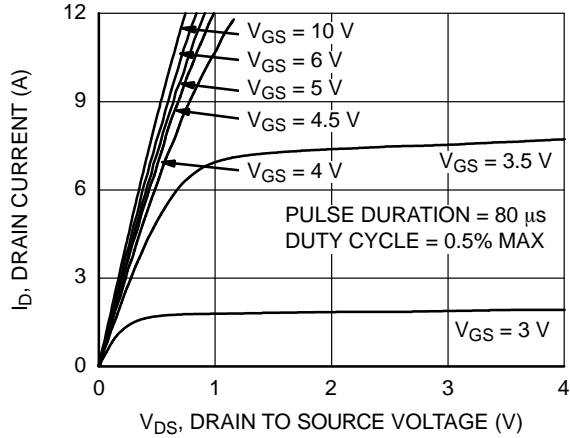


Figure 7. Saturation Characteristics

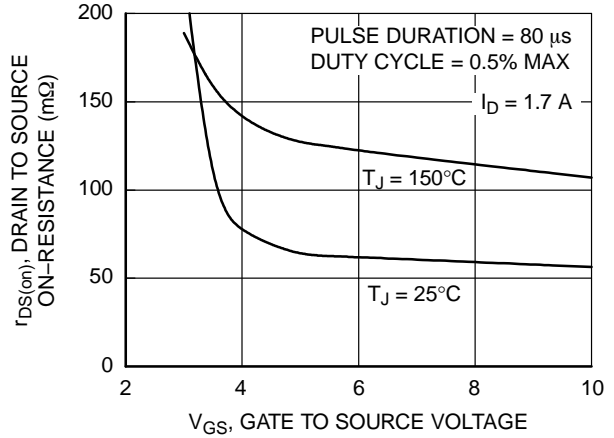


Figure 8. Drain to Source On-Resistance Variation vs. Gate to Source Voltage

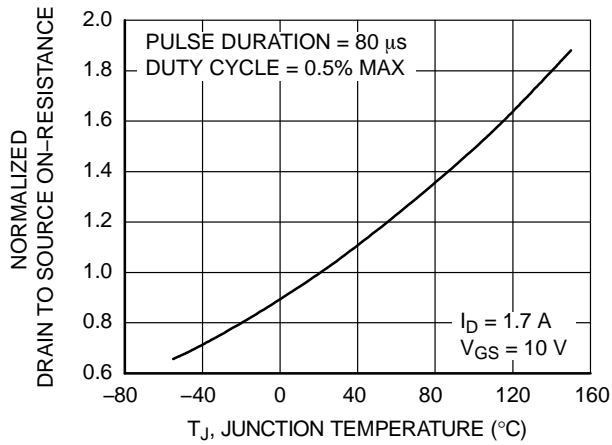


Figure 9. Normalized Drain to Source On-Resistance vs. Junction Temperature

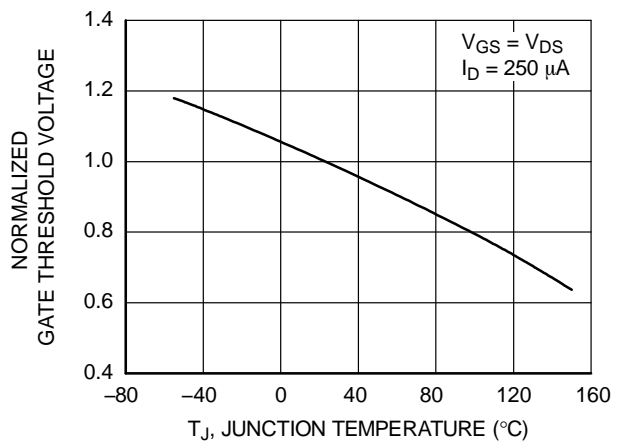
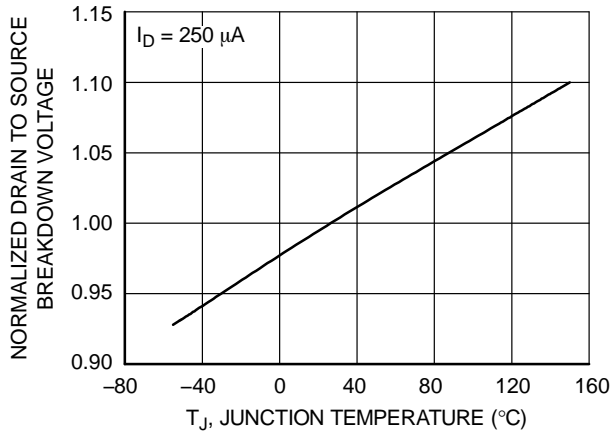


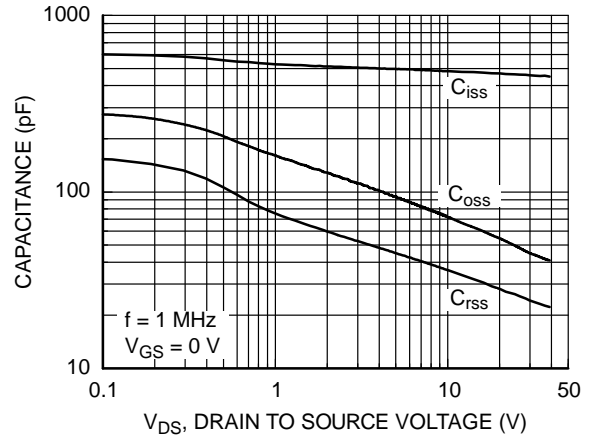
Figure 10. Normalized Gate Threshold Voltage vs. Junction Temperature

# FDN5632N-F085

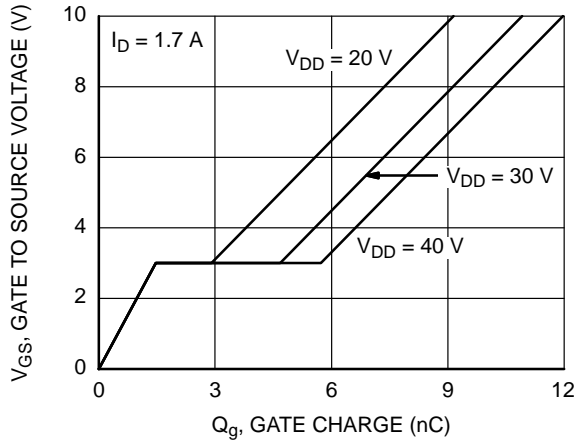
## TYPICAL CHARACTERISTICS



**Figure 11. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature**



**Figure 12. Capacitance vs. Drain to Source Voltage**



**Figure 13. Gate Charge vs. Gate to Source Voltage**

### PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping†
FDN5632N-F085	5632	SOT-23/SUPERSOT-23, 3 LEAD, 1.4x2.9 (Pb-Free, Halide Free)	7"	8 mm	3000 / Tape & Reel

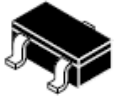
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

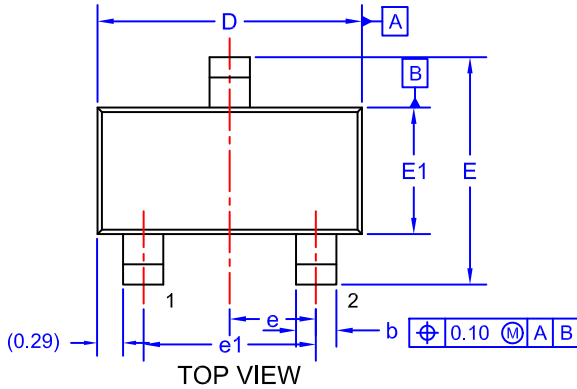
ON Semiconductor®



### SOT-23/SUPERSOT™ -23, 3 LEAD, 1.4x2.9

CASE 527AG  
ISSUE A

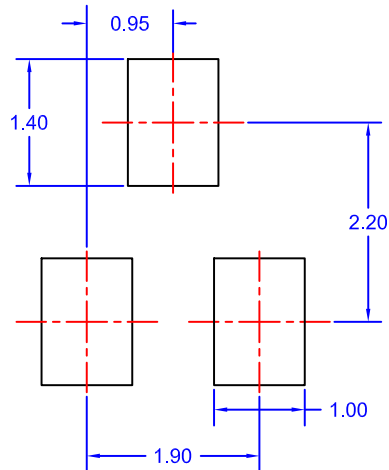
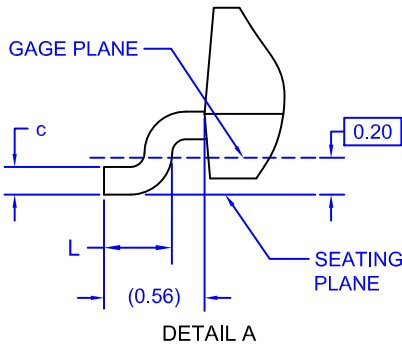
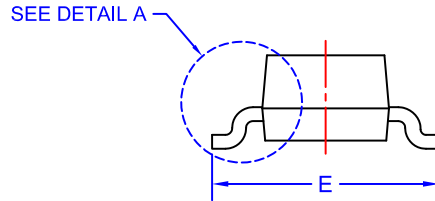
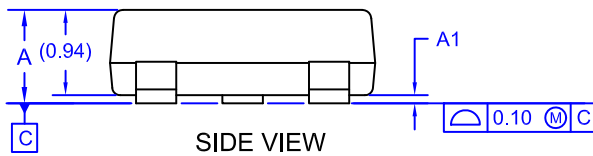
DATE 09 DEC 2019



NOTES: UNLESS OTHERWISE SPECIFIED

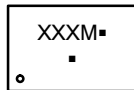
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MIN.	NOM.	MAX.
A	0.85	0.95	1.12
A1	0.00	0.05	0.10
b	0.370	0.435	0.508
c	0.085	0.150	0.180
D	2.80	2.92	3.04
E	2.31	2.51	2.71
E1	1.20	1.40	1.52
e	0.95 BSC		
e1	1.90 BSC		
L	0.33	0.38	0.43



\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

#### GENERIC MARKING DIAGRAM\*



- XXX = Specific Device Code
- M = Month Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>SOT-23/SUPERSOT-23, 3 LEAD, 1.4X2.9</b>	<b>PAGE 1 OF 1</b>

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